TRILAYER RESIST ORGANIC LAYER ETCH

ABSTRACT OF THE DISCLOSURE

A method of forming dual damascene features in a porous low-k dielectric layer is provided. Vias are formed in the porous low-k dielectric layer. An organic planarization layer is formed over the porous low-k dielectric layer, wherein the organic layer fills the vias. A photoresist mask is formed over the organic planarization layer. Features are etched into the organic planarization layer comprising providing a CO_2 containing etch gas and forming a plasma from the CO_2 containing etch gas, which etches the organic planarization layer. Trenches are etched into the porous low-k dielectric layer using the organic planarization layer as a mask. The organic planarization layer is stripped.

(Fig. 1)